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## **Electronic supplementary information**

Atomistic prediction on the configuration- and temperature-dependent dielectric

constant of  $Be_{0.25}Mg_{0.75}O$  superlattice as a high- $\kappa$  dielectric layer

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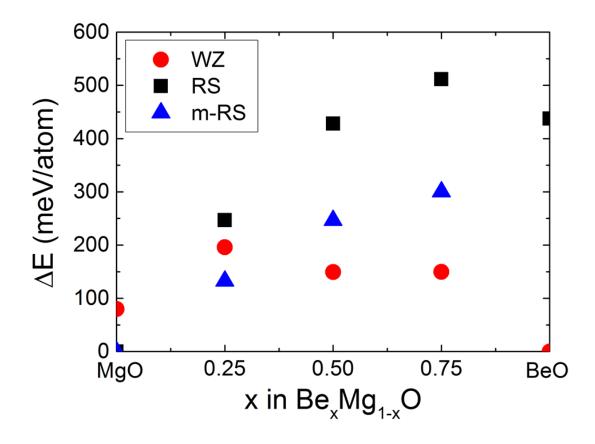
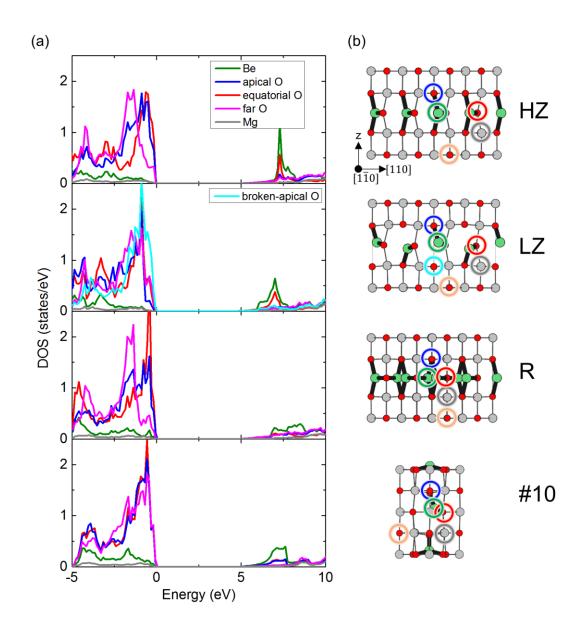


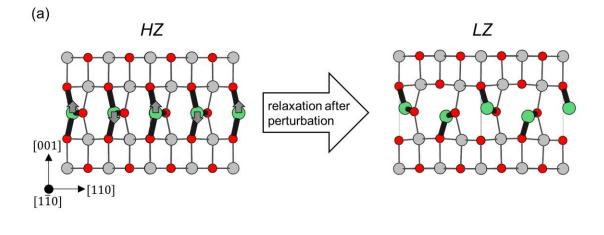
Figure S1.

Calculated  $\Delta E$  of WZ, RS, m-RS Be<sub>x</sub>Mg<sub>1-x</sub>O in 8-atom cell.





(a) Partial density of states of HZ, LZ, R, and #10 and (b) corresponding atoms in each configuration marked by circles.



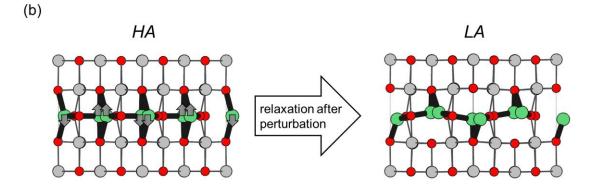


Figure S3.

Atomic positions of (a) *HZ* and *LZ* (b) *HA* and *LA*. The gray arrows indicate the atomic displacement induced by the phonon modes with the most negative eigenvalue at  $\Gamma$  of the high- $\kappa$ -type. When the atomic structure of the high- $\kappa$ -type is relaxed after a small perturbation along the atomic displacement by this phonon mode, configurations change from the high- $\kappa$ -type to the low- $\kappa$ -type.